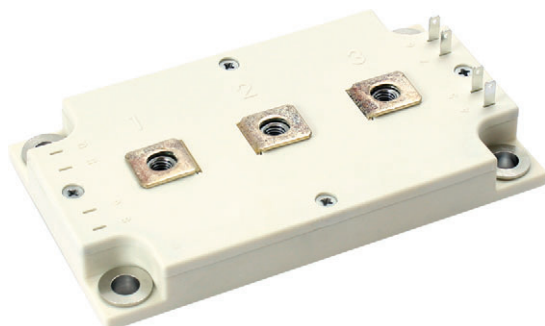


Dual INT-A-PAK Low Profile “Half Bridge” (Standard Speed IGBT), 300 A



Dual INT-A-PAK Low Profile

FEATURES

- TrenchStop IGBT technology
- Standard: optimized for hard switching speed
- Low $V_{CE(on)}$
- Square RBSOA
- Gen 4 FRED Pt[®] dices technology
- Industry standard package
- Al_2O_3 DBC
- UL approved file E78996 
- Designed for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc299912



RoHS
COMPLIANT

PRIMARY CHARACTERISTICS

V_{CES}	600 V
I_C DC at $T_C = 100\text{ }^{\circ}\text{C}$	300 A
$V_{CE(on)}$ (typical) at 300 A, $25\text{ }^{\circ}\text{C}$	1.15 V
Speed	DC to 1 kHz
Package	Dual INT-A-PAK low profile
Circuit configuration	Half bridge

BENEFITS

- Increased operating efficiency
- Performance optimized as output inverter stage for TIG welding machines
- Direct mounting on heatsink
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C ⁽¹⁾	$T_C = 25\text{ }^{\circ}\text{C}$	466	A
		$T_C = 80\text{ }^{\circ}\text{C}$	349	
Pulsed collector current	I_{CM}	$T_C = 175\text{ }^{\circ}\text{C}$, $t_p = 6\text{ ms}$, $V_{GE} = 15\text{ V}$	1500	
Clamped inductive load current	I_{LM}		700	
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	260	W
		$T_C = 80\text{ }^{\circ}\text{C}$	192	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation (IGBT)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	882	W
		$T_C = 80\text{ }^{\circ}\text{C}$	559	
Maximum power dissipation (diode)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	441	W
		$T_C = 80\text{ }^{\circ}\text{C}$	279	
RMS isolation voltage	V_{ISOL}	Any terminal to case ($V_{RMS} t = 1\text{ s}$, $T_J = 25\text{ }^{\circ}\text{C}$)	3500	V

Note

⁽¹⁾ Maximum continuous collector current must be limited to 500 A to do not exceed the maximum temperature of terminals

**ELECTRICAL SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}$, $I_C = 800\text{ }\mu\text{A}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 300\text{ A}$	-	1.15	1.47	
		$V_{GE} = 15\text{ V}$, $I_C = 300\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.16	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 4\text{ mA}$	3.8	5.0	6.3	μA
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$	-	1.2	200	
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	380	-	
Diode forward voltage drop	V_{FM}	$I_{FM} = 300\text{ A}$	-	1.56	2.02	V
		$I_{FM} = 300\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.45	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 75\text{ A}$, $V_{CC} = 520\text{ V}$, $V_{GE} = 15\text{ V}$	-	1863	-	nC
Gate-to-emitter charge (turn-on)	Q_{ge}		-	296	-	
Gate-to-collector charge (turn-on)	Q_{gc}		-	540	-	
Turn-on switching loss	E_{on}	$I_C = 300\text{ A}$, $V_{CC} = 300\text{ V}$, $V_{GE} = 15\text{ V}$, $R_g = 1.5\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	2.1	-	mJ
Turn-off switching loss	E_{off}		-	13.9	-	
Total switching loss	E_{tot}		-	16	-	
Turn-on switching loss	E_{on}	$I_C = 300\text{ A}$, $V_{CC} = 300\text{ V}$, $V_{GE} = 15\text{ V}$, $R_g = 1.5\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2	-	ns
Turn-off switching loss	E_{off}		-	20	-	
Total switching loss	E_{tot}		-	22	-	
Turn-on delay time	$t_{d(on)}$		-	19	-	
Rise time	t_r		-	75	-	
Turn-off delay time	$t_{d(off)}$		-	419	-	
Fall time	t_f		-	194	-	
Reverse bias safe operating area	RBSOA	$T_J = 175\text{ }^{\circ}\text{C}$, $I_C = 700\text{ A}$, $R_g = 1.5\text{ }\Omega$, $V_{GE} = +15\text{ V/0 V}$, $V_{CC} = 300\text{ V}$, $V_p = 600\text{ V}$	Fullsquare			
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}$, $di_F/dt = 500\text{ A}/\mu\text{s}$, $V_{CC} = 200\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	152	-	ns
Diode peak reverse current	I_{rr}		-	24	-	A
Diode recovery charge	Q_{rr}		-	1.81	-	μC
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}$, $di_F/dt = 500\text{ A}/\mu\text{s}$, $V_{CC} = 200\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	201	-	ns
Diode peak reverse current	I_{rr}		-	39	-	A
Diode recovery charge	Q_{rr}		-	3.94	-	μC

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Operating junction and storage temperature range	T_J , T_{Stg}	-40	-	175	$^{\circ}\text{C}$
Junction to case per leg	IGBT	-	-	0.17	$^{\circ}\text{C/W}$
	Diode	-	-	0.34	
Case to sink per module	R_{thCS}	-	0.05	-	
Mounting torque	case to heatsink: M6 screw	4	-	6	Nm
	case to terminal 1, 2, 3: M5 screw	2	-	5	
Weight		-	270	-	g

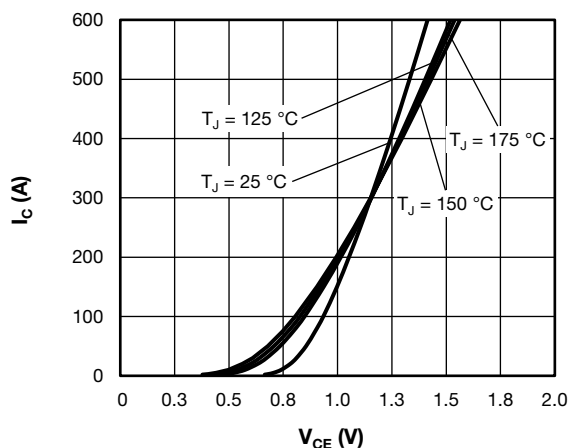


Fig. 1 - Typical Trench IGBT Output Characteristics,
 $V_{GE} = 15 \text{ V}$

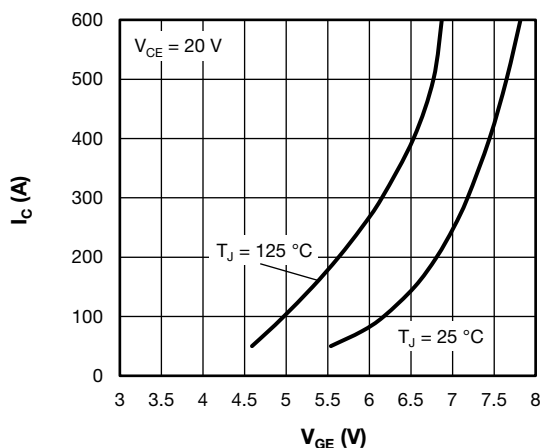


Fig. 4 - Typical Trench IGBT Transfer Characteristics

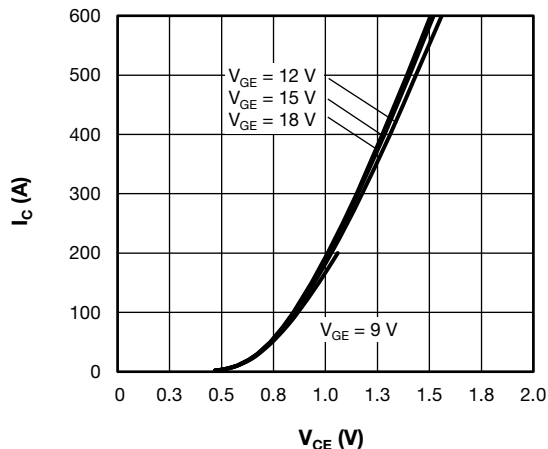


Fig. 2 - Typical Trench IGBT Output Characteristics,
 $T_J = 125 \text{ °C}$

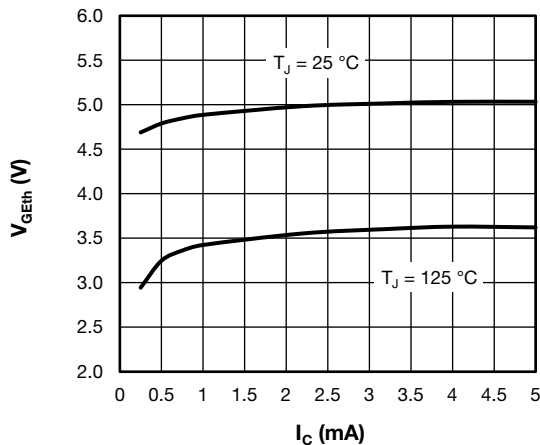


Fig. 5 - Typical Trench IGBT Gate Threshold Voltage

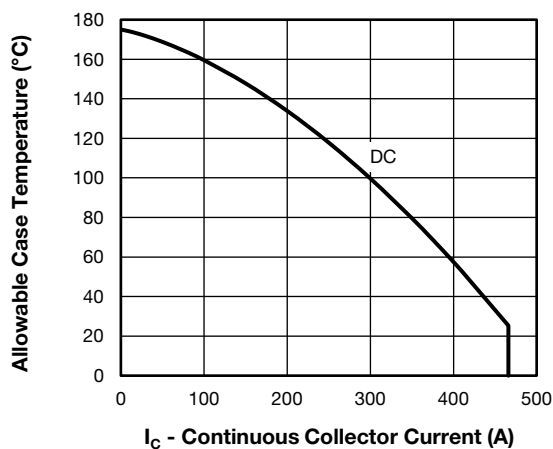


Fig. 3 - Maximum Trench IGBT Continuous Collector Current vs.
Case Temperature

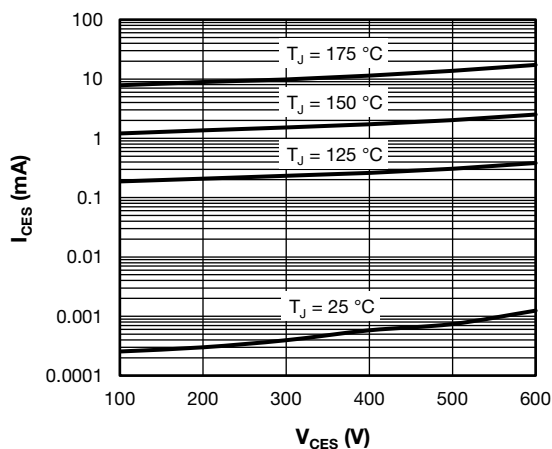


Fig. 6 - Typical trench IGBT Zero Gate Voltage Collector Current

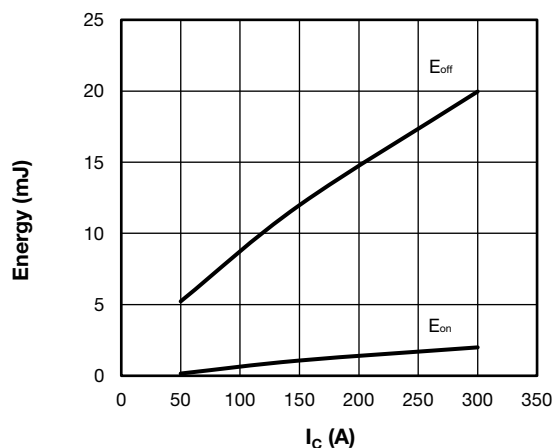


Fig. 7 - Typical Trench IGBT Energy Loss vs. I_C ,
(with Antiparallel Diode), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 1.5\ \Omega$,
 $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

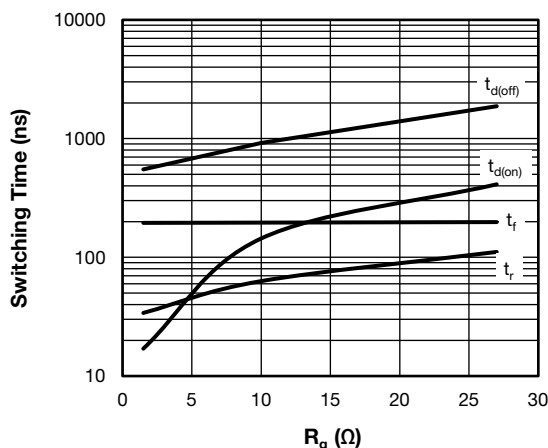


Fig. 10 - Typical Trench IGBT Switching Time vs. R_g
(with Antiparallel Diode), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 300\text{ A}$,
 $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

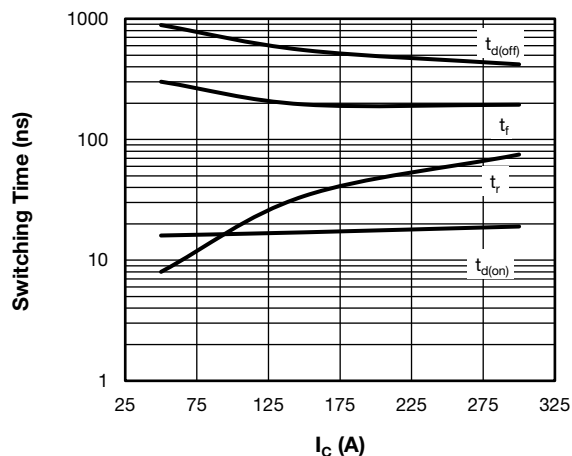


Fig. 8 - Typical Trench IGBT Switching Time vs. I_C ,
(with Antiparallel Diode), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 1.5\ \Omega$,
 $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

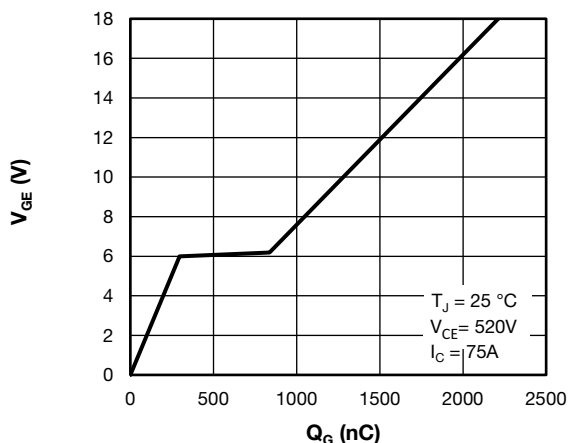


Fig. 11 - Typical Trench IGBT Gate Charge vs.
Gate to Emitter Voltage

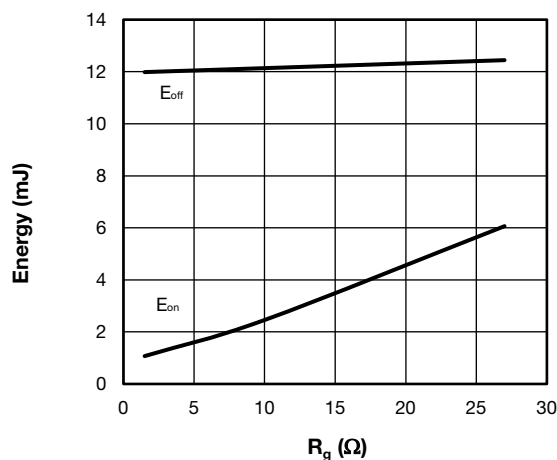


Fig. 9 - Typical Trench IGBT Energy Loss vs. R_g
(with Antiparallel Diode), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 300\text{ A}$,
 $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

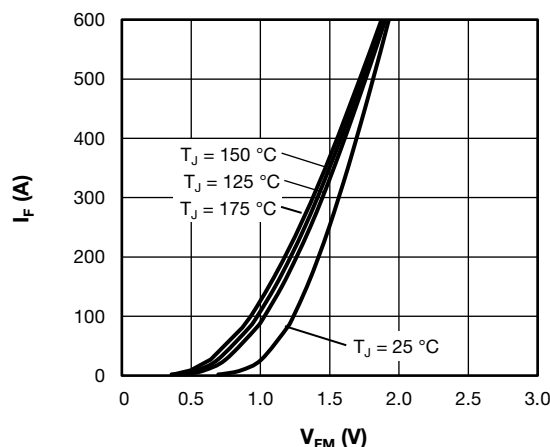


Fig. 12 - Typical Antiparallel Diode Forward Characteristics

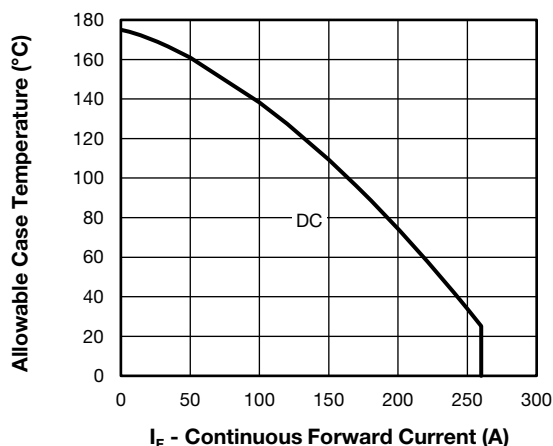


Fig. 13 - Maximum Antiparallel Diode Continuous Forward Current vs. Case Temperature

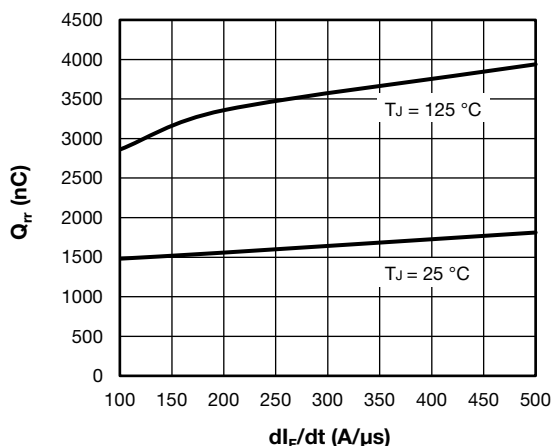


Fig. 16 - Typical Antiparallel Diode Reverse Recovery Charge vs. dI_F/dt , $I_F = 50\text{ A}$, $V_{CC} = 200\text{ V}$

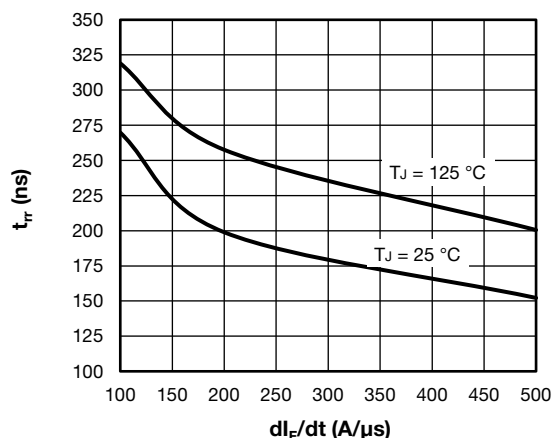


Fig. 14 - Typical Antiparallel Diode Reverse Recovery Time vs. dI_F/dt , $I_F = 50\text{ A}$, $V_{CC} = 200\text{ V}$

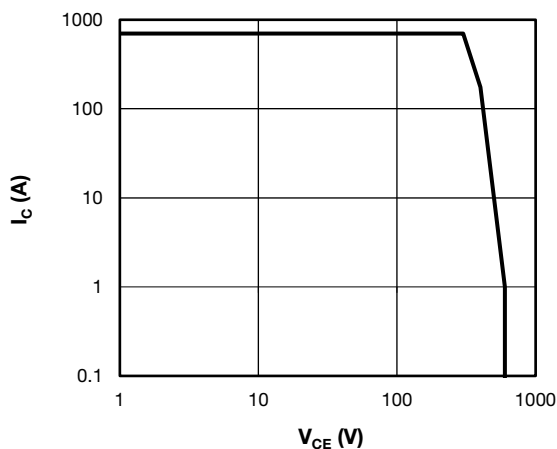


Fig. 17 - Trench IGBT Reverse BIAS SOA
 $T_J = 175^\circ\text{C}$, $I_C = 700\text{ A}$, $R_{\theta} = 1.5^\circ\text{C/W}$, $V_{GE} = +15\text{ V/O V}$,
 $V_{CC} = 300\text{ V}$, $V_p = 600\text{ V}$

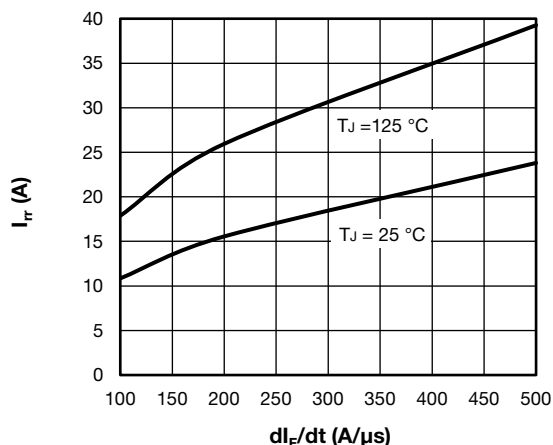


Fig. 15 - Typical Antiparallel Diode Reverse Recovery Current vs. dI_F/dt , $I_F = 50\text{ A}$, $V_{CC} = 200\text{ V}$

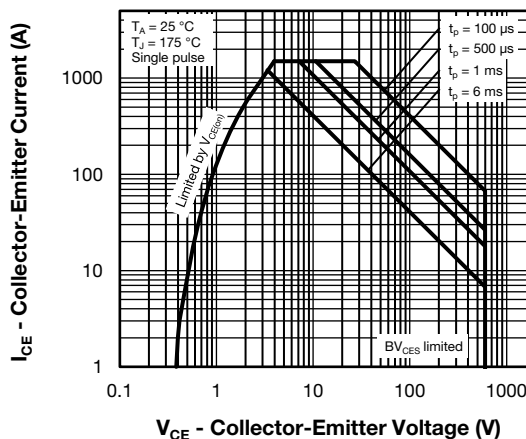


Fig. 18 - Trench IGBT Safe Operating Area

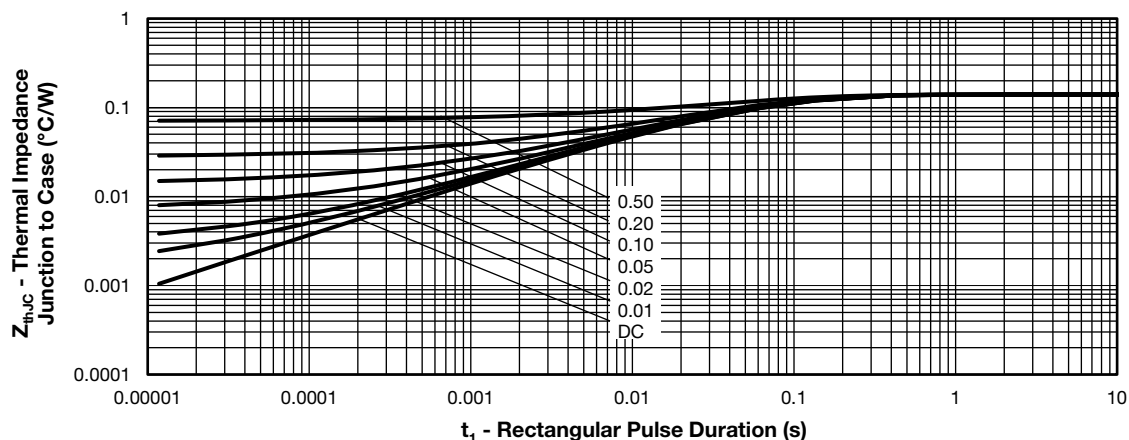


Fig. 19 - Maximum Trench IGBT Thermal Impedance Z_{thJC} Characteristics (IGBT)

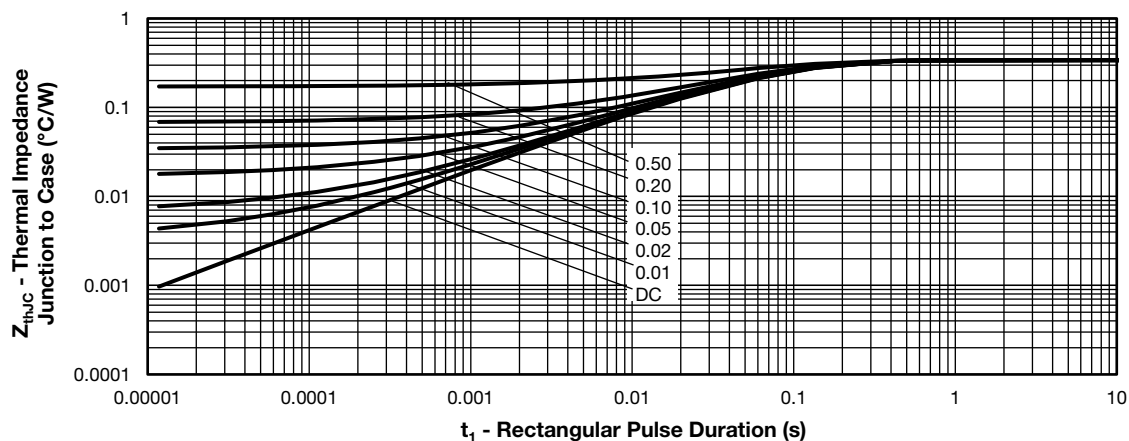


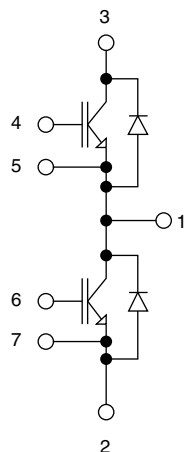
Fig. 20 - Maximum Antiparallel Diode Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	G	T	300	T	D	60	S
	1	2	3	4	5	6	7
1	-	Insulated gate bipolar transistor (IGBT)					
2	-	T = Trench IGBT technology					
3	-	Current rating (300 = 300 A)					
4	-	Circuit configuration (T = half bridge)					
5	-	Package indicator (D = dual INT-A-PAK low profile)					
6	-	Voltage rating (60 = 600 V)					
7	-	Speed / type (S = standard speed IGBT)					



CIRCUIT CONFIGURATION

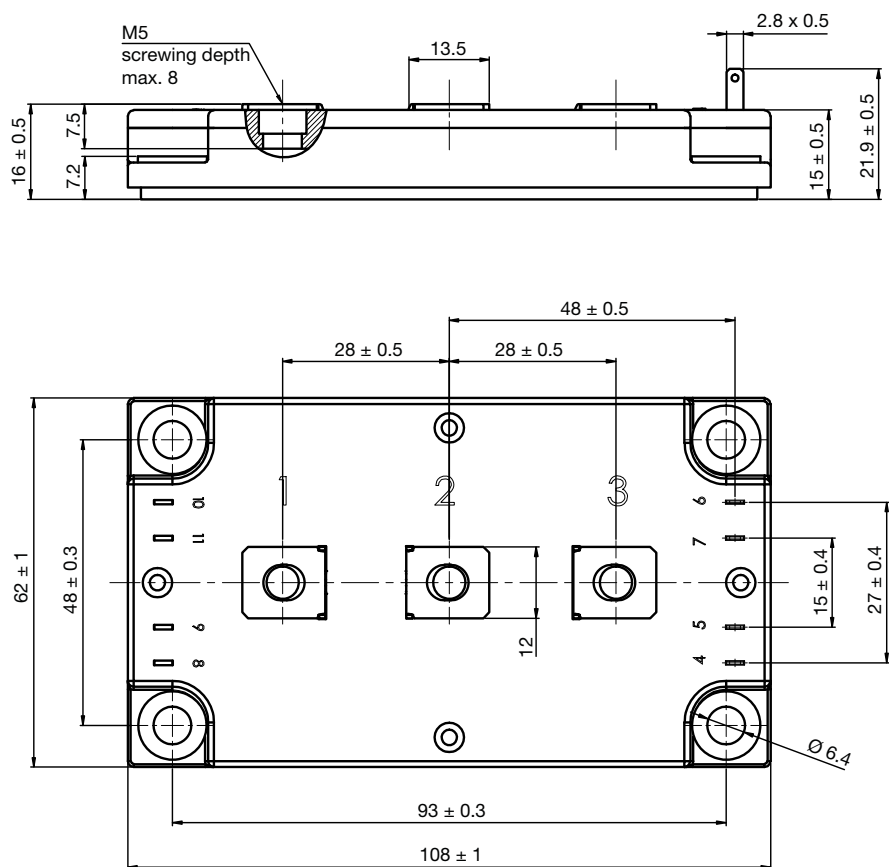


LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95435
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Dual INT-A-PAK Low Profile

DIMENSIONS in millimeters





Disclaimer

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